

Product Specification

2SB616

DESCRIPTION

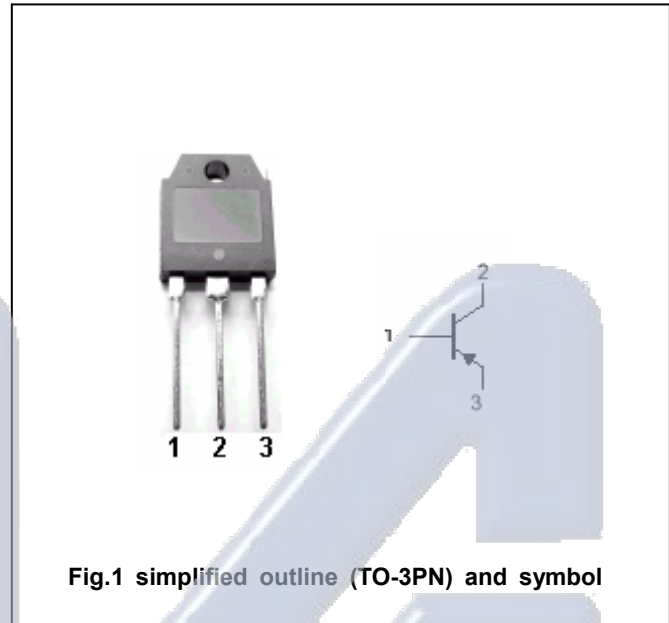
- With TO-3PN package
- Complement to type 2SD586

APPLICATIONS

- For power amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings($T_c=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-100	V
V_{CEO}	Collector-emitter voltage	Open base	-100	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-5	A
P_C	Collector power dissipation	$T_c=25$	60	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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2SB616**CHARACTERISTICS**

Tj=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C = -30\text{mA}$; $I_B = 0$	-100			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C = -1\text{mA}$; $I_E = 0$	-100			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E = -1\text{mA}$; $I_C = 0$	-5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C = -3\text{A}$; $I_B = -0.3\text{A}$			-1.5	V
V_{BE}	Base-emitter on voltage	$I_C = -1\text{A}$; $V_{CE} = -5\text{V}$			-1.5	V
I_{CBO}	Collector cut-off current	$V_{CB} = -100\text{V}$; $I_E = 0$			-0.1	mA
I_{EBO}	Emitter cut-off current	$V_{EB} = -5\text{V}$; $I_C = 0$			-0.1	mA
h_{FE-1}	DC current gain	$I_C = -1\text{A}$; $V_{CE} = -5\text{V}$	50			
f_T	Transition frequency	$I_C = -1\text{A}$; $V_{CE} = -5\text{V}$		11		MHz
C_{OB}	Collector output capacitance	$I_E = 0$; $f = 1\text{MHz}$; $V_{CB} = -10\text{V}$		140		pF

Electrónica S.A. de C.V.

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PACKAGE OUTLINE

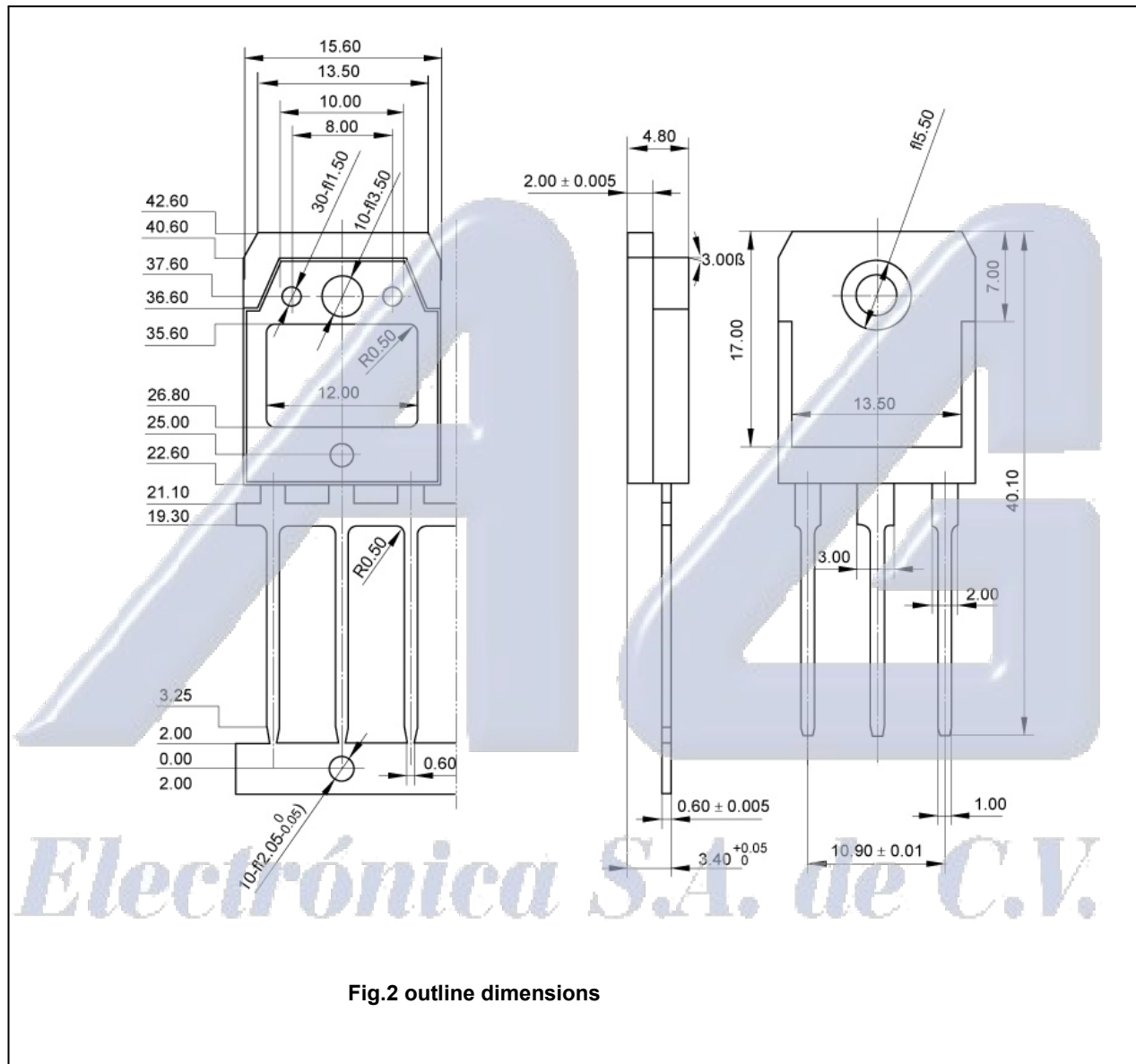


Fig.2 outline dimensions